Silicon PNP Power Transistors 2SB1086A

DESCRIPTION

- With TO-126 package
- Complement to type 2SD1563A
- Low collector saturation voltage
- Large current capability

APPLICATIONS

- Designed for use in low frequency power amplifier applications

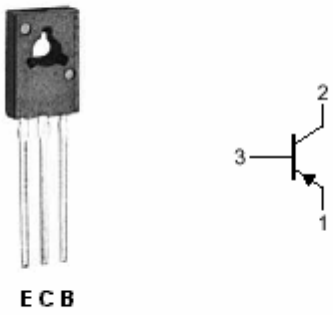

Fig.1 simplified outline (TO-126) and symbol

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-160	V
V_{CEO}	Collector-emitter voltage	Open base	-160	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-1.5	A
I_{CM}	Collector current -peak		-3.0	A
P_D	Total power dissipation	T_C=25℃	10	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-1mA ;I_B=0	-160			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-50 μ A ;I_E=0	-160			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-50 μ A ;I_C=0	-5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-1.0A ;I_B=-0.1A			-2.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-1.0A ;I_B=-0.1A			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-120V; I_E=0			-1.0	μ A
I_{EBO}	Emitter cut-off current	V_{EB}=-4V; I_C=0			-1.0	μ A
h_{FE}	DC current gain	I_C=-0.1A ; V_{CE}=-5V	56		270	
f_T	Transition frequency	I_C=-0.1A ; V_{CE}=-5V		50		MHz
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=-10V;f=1MHz		30		pF

PACKAGE OUTLINE

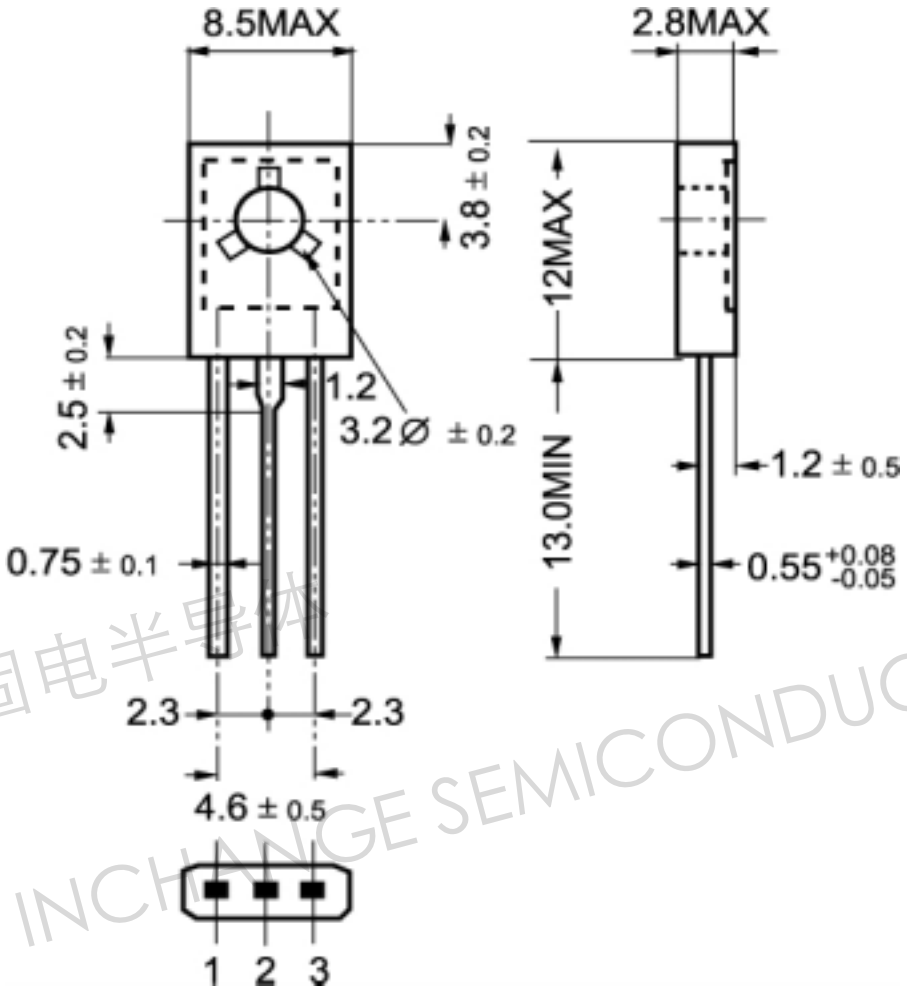

Fig.2 Outline dimensions